

HiPerFET™ Power MOSFETs Q-Class

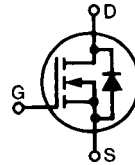
IXFH 80N10Q
IXFT 80N10Q

V_{DSS} = 100 V
I_{D25} = 80 A
R_{DS(on)} = 15 mΩ

t_{rr} ≤ 200ns

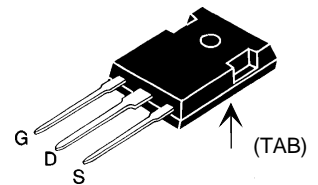
N-Channel Enhancement Mode
Avalanche Rated, High dV/dt
Low Gate Charge and Capacitances

Preliminary data

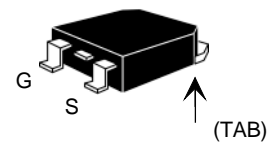


Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	100	V
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	100	V
V _{GS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	80	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	320	A
I _{AR}	T _C = 25°C	80	A
E _{AR}	T _C = 25°C	30	mJ
E _{AS}	T _C = 25°C	1.5	J
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	5	V/ns
P _D	T _C = 25°C	360	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6 mm (0.062 in.) from case for 10 s	300	°C
M _d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	4	g

TO-247 AD (IXFH)



TO-268 (IXFT) Case Style



G = Gate D = Drain
S = Source TAB = Drain

Features

- IXYS advanced low gate charge process
- International standard packages
- Low gate charge and capacitance
 - easier to drive
 - faster switching
- Low R_{DS(on)}
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

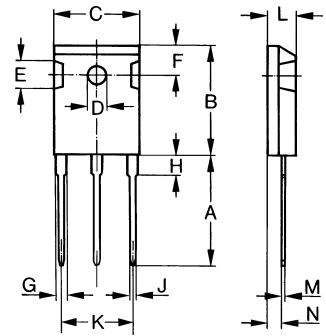
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	100		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4 mA	2.0		V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±100 nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0 V	T _J = 25°C		25 μA
		T _J = 125°C		1 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			15 mΩ

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$, pulse test	30	45	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF
C_{oss}			1600	pF
C_{rss}			870	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1.5\ \Omega$ (External)		30	ns
t_r			70	ns
$t_{d(off)}$			68	ns
t_f			30	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		180	nC
Q_{gs}			36	nC
Q_{gd}			95	nC
R_{thJC}	(TO-247)		0.35	K/W
R_{thCK}			0.25	K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			80 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			320 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 50\text{ V}$		0.85	200 ns
Q_{RM}				μC
I_{RM}			8	A

TO-247 AD (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D ³ PAK)		Dim.		Millimeter		Inches	
		Min.	Max.	Min.	Max.	Min.	Max.
	A	4.9	5.1	.193	.201		
	A ₁	2.7	2.9	.106	.114		
	A ₂	.02	.25	.001	.010		
	b	1.15	1.45	.045	.057		
	b ₂	1.9	2.1	.75	.83		
	C	.4	.65	.016	.026		
	D	13.80	14.00	.543	.551		
	E	15.85	16.05	.624	.632		
	E ₁	13.3	13.6	.524	.535		
	e	5.45 BSC		.215 BSC			
	H	18.70	19.10	.736	.752		
	L	2.40	2.70	.094	.106		
	L ₁	1.20	1.40	.047	.055		
	L ₂	1.00	1.15	.039	.045		
L ₃	0.25 BSC		.010 BSC				
L ₄	3.80	4.10	.150	.161			

Min. Recommended Footprint

